

Boncheol Ku

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Compliance-Free, Digital SET and Analog RESET Synaptic Characteristics of Sub-Tantalum Oxide Based Neuromorphic Device. Scientific Reports, 2018, 8, 1228.	3.3	91
2	The coexistence of threshold and memory switching characteristics of ALD HfO ₂ memristor synaptic arrays for energy-efficient neuromorphic computing. Nanoscale, 2020, 12, 14120-14134.	5.6	88
3	Interface engineering of ALD HfO ₂ -based RRAM with Ar plasma treatment for reliable and uniform switching behaviors. Journal of Alloys and Compounds, 2018, 735, 1181-1188.	5.5	85
4	Influence of oxygen vacancies in ALD HfO _{2-x} thin films on non-volatile resistive switching phenomena with a Ti/HfO _{2-x} /Pt structure. Applied Surface Science, 2018, 434, 822-830.	6.1	85
5	Bio-realistic synaptic characteristics in the cone-shaped ZnO memristive device. NPG Asia Materials, 2019, 11, .	7.9	55
6	Study of in Situ Silver Migration in Amorphous Boron Nitride CBRAM Device. ACS Applied Materials & Interfaces, 2019, 11, 23329-23336.	8.0	52
7	Engineering synaptic characteristics of TaO _x /HfO ₂ bi-layered resistive switching device. Nanotechnology, 2018, 29, 415204.	2.6	46
8	Two-terminal artificial synapse with hybrid organic-inorganic perovskite (CH ₃ NH ₃)PbI ₃ and low operating power energy (1/447 Åf/1/4m ²). Journal of Alloys and Compounds, 2020, 833, 155064.	5.5	41
9	Ar ion plasma surface modification on the heterostructured TaO _x /InGaZnO thin films for flexible memristor synapse. Journal of Alloys and Compounds, 2020, 822, 153625.	5.5	39
10	Analog Synaptic Transistor with Al-Doped HfO ₂ Ferroelectric Thin Film. ACS Applied Materials & Interfaces, 2021, 13, 52743-52753.	8.0	37
11	Structural engineering of tantalum oxide based memristor and its electrical switching responses using rapid thermal annealing. Journal of Alloys and Compounds, 2018, 759, 44-51.	5.5	33
12	Cellulose Nanocrystal Based Bio-Memristor as a Green Artificial Synaptic Device for Neuromorphic Computing Applications. Advanced Materials Technologies, 2022, 7, 2100744.	5.8	29
13	Improved resistive switching and synaptic characteristics using Ar plasma irradiation on the Ti/HfO ₂ interface. Journal of Alloys and Compounds, 2019, 797, 277-283.	5.5	28
14	Improved switching and synapse characteristics using PEALD SiO ₂ thin film in Cu/SiO ₂ /ZrO ₂ /Pt device. Applied Surface Science, 2021, 547, 149140.	6.1	12